# NSN 5961-01-211-8444

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# Inclosure Material:

Metal

# **Overall Length:**

Between 0.970 inches and 1.218 inches

# Overall Diameter:

0.505 inches

# Mounting Facility Quantity:

1

## Internal Configuration:

Junction contact

# Joint Electronic Device Engineering Council/jedec/case Outline Designation:

To-111

## **Mounting Method:**

Threaded stud

## **Overall Width Across Flats:**

Between 0.423 inches and 0.438 inches

## Semiconductor Material:

Silicon

## Voltage Rating In Volts Per Characteristic:

80.0 breakdown voltage, collector-to-emitter, base open

## **Current Rating Per Characteristic:**

10.00 amperes source cutoff current and 30.00 nanoamperes base current, dc preset

## Power Rating Per Characteristic:

30.0 watts small-signal input power, common-collector absolute

## Transfer Ratio:

50.0 static forward current transfer ratio, common-emitter and 150.0 static forward current transfer ratio, common-emitter

## Maximum Operating Tempurature Per Measurement Point:

200.0 degrees celsius junction

## **Special Features:**

High power switching transistor; junction pattern arrangement: npn

# Terminal Type And Quantity:

2 uninsulated wire lead w/terminal lug and 1 wire hook

# Shelf Life:

N/a

# Unit Of Measure:

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## Demilitarization:

Yes - demil/mli

Fiig:

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